

Microwave Long Pulse Power Silicon NPN Transistor

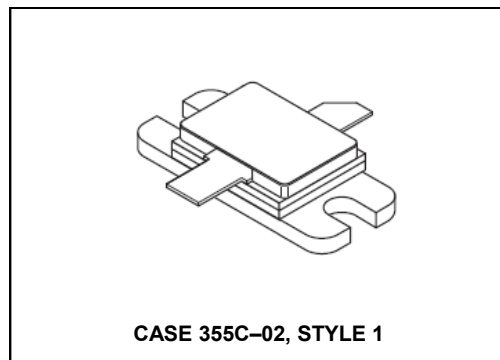
120W (peak), 960–1215MHz

Rev. V1

Designed for 960–1215 MHz long pulse common base amplifier applications such as JTIDS and Mode S transmitters.

- Guaranteed performance @ 1.215 GHz, 36 Vdc
Output power = 120 W Peak
Gain = 7.6 dB min., 8.5 dB (typ.)
- 100% tested for load mismatch at all phase angles with 3:1 VSWR
- Hermetically sealed industry standard package
- Silicon nitride passivated
- Gold metalized, emitter ballasted for long life and resistance to metal migration
- Internal input and output matching for broadband operation

Product Image



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	55	Vdc
Collector–Base Voltage	V_{CBO}	55	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Peak (1)	I_C	15	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1), (2) Derate above 25°C	P_D	380 2.17	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +200	$^\circ\text{C}$
Junction Temperature	T_J	200	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.46	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	55	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	55	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 36 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	25	mAdc

NOTES:

(continued)

- Under pulse RF operating conditions.
- These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
- Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

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ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20	—	—	—
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FUNCTIONAL TESTS (7.0 μs Pulses @ 54% duty cycle for 3.4 ms; then off for 4.5 ms; overall duty cycle = 23%)

Common-Base Amplifier Power Gain ($V_{CC} = 36 \text{ Vdc}$, $P_{out} = 120 \text{ W Peak}$, $f = 1215 \text{ MHz}$)	G_{PB}	7.6	8.5	—	dB
Collector Efficiency ($V_{CC} = 36 \text{ Vdc}$, $P_{out} = 120 \text{ W Peak}$, $f = 1215 \text{ MHz}$)	η	50	55	—	%
Load Mismatch ($V_{CC} = 36 \text{ Vdc}$, $P_{out} = 120 \text{ W Peak}$, $f = 1215 \text{ MHz}$, VSWR = 3:1 All Phase Angles)	Ψ	No Degradation in Output Power			

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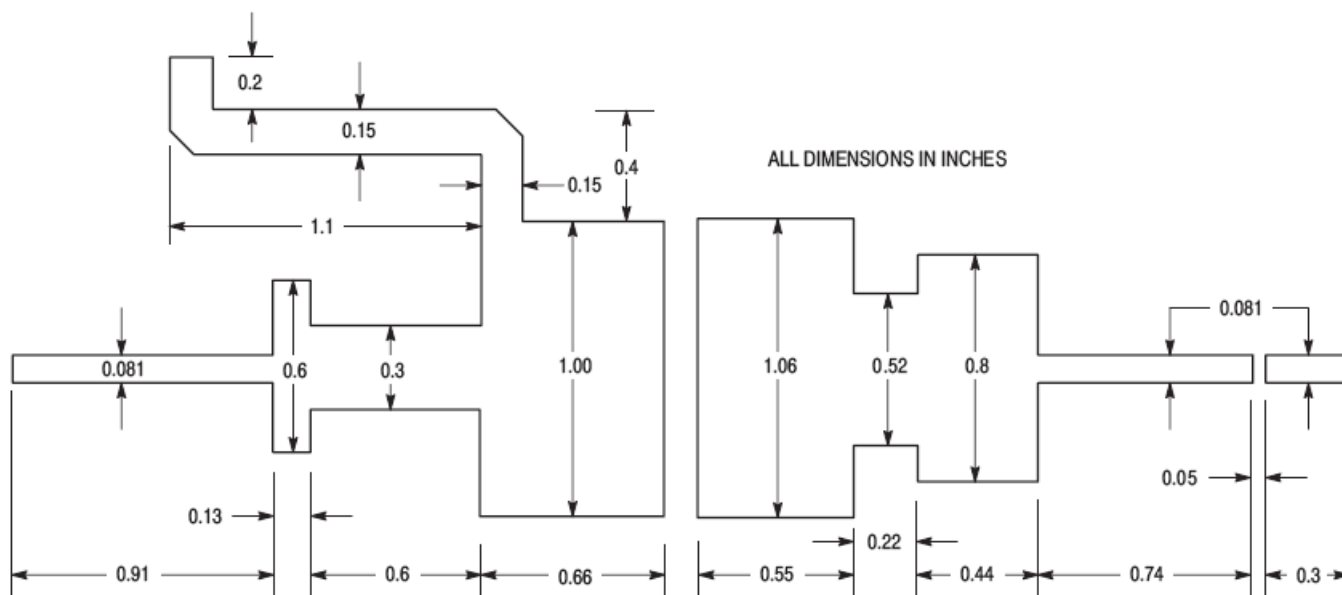
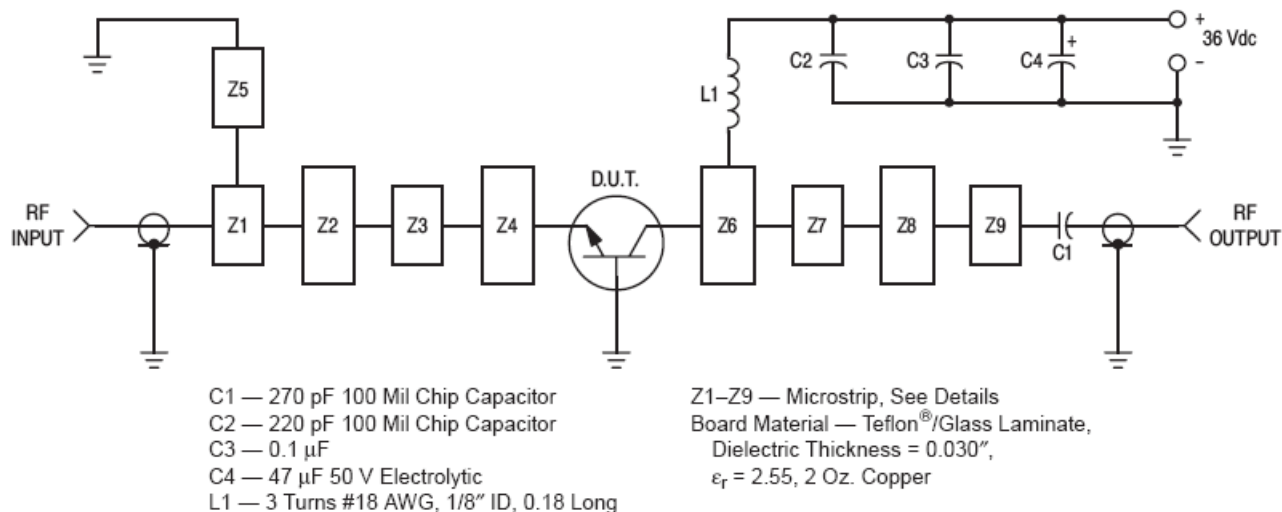


Figure 1. Test Circuit

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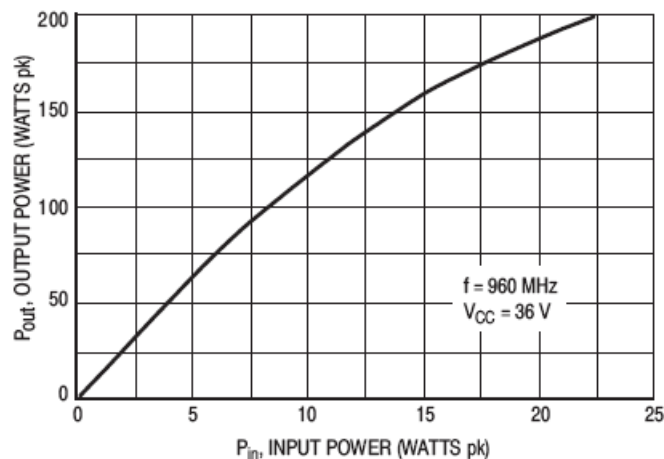


Figure 2. Output Power versus Input Power

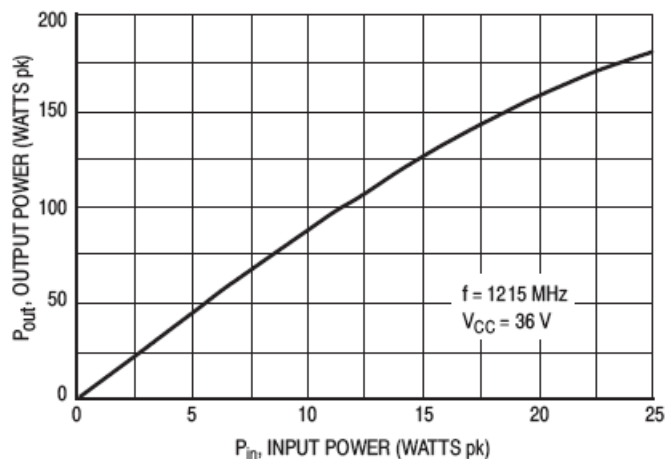


Figure 3. Output Power versus Input Power

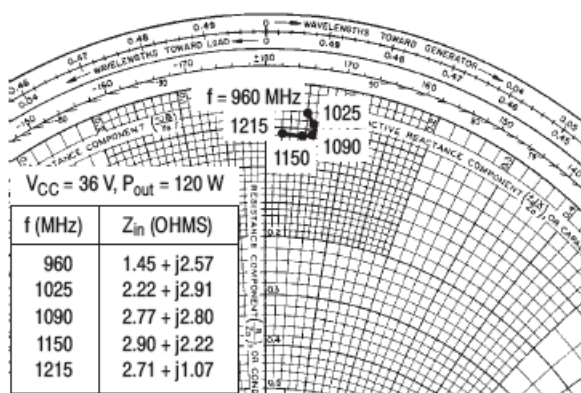
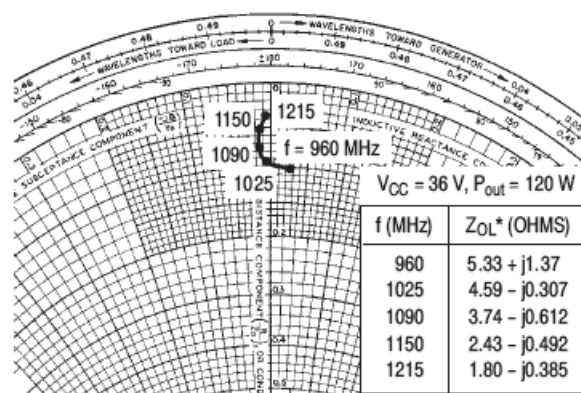


Figure 4. Series Equivalent Input Impedances



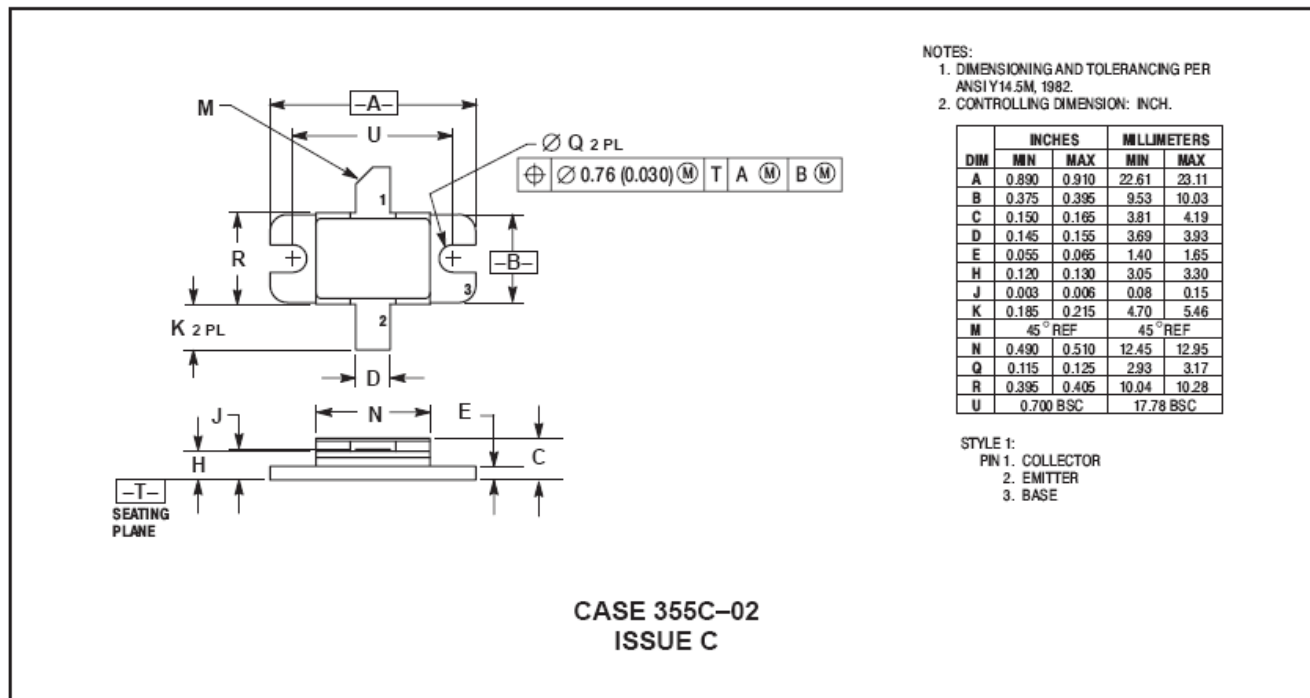
Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 5. Series Equivalent Output Impedance

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PACKAGE DIMENSIONS



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